

# Emanuel Tutuc

## List of Publications by Year in descending order

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149  
papers

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31902

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g-index

150  
all docs

150  
docs citations

150  
times ranked

24530  
citing authors

#	ARTICLE	IF	CITATIONS
1	Twisted 2D electronic and photonic materials and devices. Applied Physics Letters, 2022, 120, 130401.	1.5	0
2	Bulk and edge properties of twisted double bilayer graphene. Nature Physics, 2022, 18, 48-53.	6.5	14
3	Emergence of correlations in alternating twist quadrilayer graphene. Nature Materials, 2022, 21, 884-889.	13.3	28
4	The marvels of moiré materials. Nature Reviews Materials, 2021, 6, 201-206.	23.3	262
5	Electron mobility in monolayer WS <sub>2</sub> encapsulated in hexagonal boron-nitride. Applied Physics Letters, 2021, 118, .	1.5	17
6	Epitaxial Al-InAs Heterostructures as Platform for Josephson Junction Field-Effect Transistor Logic Devices. IEEE Transactions on Electron Devices, 2021, 68, 1524-1529.	1.6	7
7	Quantum Lifetime Spectroscopy and Magnetotunneling in Double Bilayer Graphene Heterostructures. Physical Review Letters, 2021, 127, 117701.	2.9	3
8	Mean Free Path Suppression of Low-Frequency Phonons in SiGe Nanowires. Nano Letters, 2020, 20, 8384-8391.	4.5	12
9	InSb pixel loaded microwave resonator for high-speed mid-wave infrared detection. Infrared Physics and Technology, 2020, 109, 103390.	1.3	7
10	Room-Temperature Mid-Infrared Detection via Resonant Microwave Circuits. IEEE Transactions on Electron Devices, 2020, 67, 1632-1638.	1.6	4
11	Flat bands in twisted bilayer transition metal dichalcogenides. Nature Physics, 2020, 16, 1093-1096.	6.5	197
12	Tunneling and fluctuating electron-hole Cooper pairs in double bilayer graphene. Physical Review B, 2020, 101, .	1.1	17
13	Highly valley-polarized singlet and triplet interlayer excitons in van der Waals heterostructure. Physical Review B, 2019, 100, .	1.1	58
14	Correlated Insulating States in Twisted Double Bilayer Graphene. Physical Review Letters, 2019, 123, 197702.	2.9	194
15	Topological Insulators in Twisted Transition Metal Dichalcogenide Homobilayers. Physical Review Letters, 2019, 122, 086402.	2.9	333
16	Measurement of carrier lifetime in micron-scaled materials using resonant microwave circuits. Nature Communications, 2019, 10, 1625.	5.8	12
17	Evidence for moiré excitons in van der Waals heterostructures. Nature, 2019, 567, 71-75.	13.7	933
18	Mid-Infrared Detection using a Microwave Resonator Photoconductive Architecture. , 2019, , .		0

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19	Interlayer exciton laser of extended spatial coherence in atomically thin heterostructures. Nature, 2019, 576, 80-84.	13.7	120
20	Josephson Junction Field-Effect Transistors for Boolean Logic Cryogenic Applications. IEEE Transactions on Electron Devices, 2019, 66, 5367-5374.	1.6	20
21	Tunable $\hat{I}^*$ Valley Populations in Hole-Doped Trilayer $WSe_2$	2.9	23
22	Strongly Enhanced Tunneling at Total Charge Neutrality in Double-Bilayer Graphene- $WSe_2$ Heterostructures. Physical Review Letters, 2018, 120, 177702.	2.9	102
23	Photonic-crystal exciton-polaritons in monolayer semiconductors. Nature Communications, 2018, 9, 713.	5.8	197
24	Enhanced Electron Mobility in Nonplanar Tensile Strained Si Epitaxially Grown on $Si_xGe_{1-x}$ Nanowires. Nano Letters, 2018, 18, 94-100.	4.5	15
25	Strained $Si_xGe_{1-x}$ -Ge-Si core-double-shell nanowire heterostructures for simultaneous hole and electron mobility enhancement. Applied Physics Letters, 2018, 113, .	1.5	3
26	Large effective mass and interaction-enhanced Zeeman splitting of $K$ -valley electrons in $MoSe_2$ Physical Review B, 2018, 97, .	1.1	72
27	Topologically Protected Helical States in Minimally Twisted Bilayer Graphene. Physical Review Letters, 2018, 121, 037702.	2.9	175
28	Hubbard Model Physics in Transition Metal Dichalcogenide Moiré Bands. Physical Review Letters, 2018, 121, 026402.	2.9	413
29	Spin-Conserving Resonant Tunneling in Twist-Controlled $WSe_2$ -hBN- $WSe_2$ Heterostructures. Nano Letters, 2018, 18, 5967-5973.	4.5	29
30	Reconfigurable Complementary Monolayer $MoTe_2$ Field-Effect Transistors for Integrated Circuits. ACS Nano, 2017, 11, 4832-4839.	7.3	108
31	Shell morphology and Raman spectra of epitaxial $Ge^{1-x}Si_x$ and $Si^{1-x}Ge_x$ core-shell nanowires. Journal of Applied Physics, 2017, 121, 234302.	1.1	5
32	Intra-domain periodic defects in monolayer $MoS_2$ . Applied Physics Letters, 2017, 110, .	1.5	16
33	Coherent Interlayer Tunneling and Negative Differential Resistance with High Current Density in Double Bilayer Graphene- $WSe_2$ Heterostructures. Nano Letters, 2017, 17, 3919-3925.	4.5	53
34	Tunable moiré bands and strong correlations in small-twist-angle bilayer graphene. Proceedings of the National Academy of Sciences of the United States of America, 2017, 114, 3364-3369.	3.3	434
35	Interlayer tunnel field-effect transistor (ITFET): physics, fabrication and applications. Journal Physics D: Applied Physics, 2017, 50, 383002.	1.3	11
36	Density-Dependent Quantum Hall States and Zeeman Splitting in Monolayer and Bilayer $WSe_2$ Physical Review Letters, 2017, 118, 247701.	2.9	72

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37	ReS <sub>2</sub> -based interlayer tunnel field effect transistor. Journal of Applied Physics, 2017, 122, .	1.1	7
38	Transport spectroscopy in bilayer graphene using double layer heterostructures. 2D Materials, 2017, 4, 035018.	2.0	5
39	Atomically Resolved Elucidation of the Electrochemical Covalent Molecular Grafting Mechanism of Single Layer Graphene. Advanced Materials Interfaces, 2016, 3, 1600196.	1.9	11
40	DFT simulations of inter-graphene-layer coupling with rotationally misaligned hBN tunnel barriers in graphene/hBN/graphene tunnel FETs. Journal of Applied Physics, 2016, 120, .	1.1	18
41	Improved contact resistance in ReSe <sub>2</sub> thin film field-effect transistors. Applied Physics Letters, 2016, 108, .	1.5	22
42	Experimental Demonstration of Phase Modulation and Motion Sensing Using Graphene-Integrated Metasurfaces. Nano Letters, 2016, 16, 3607-3615.	4.5	84
43	High Phosphorus Dopant Activation in Germanium Using Laser Spike Annealing. IEEE Electron Device Letters, 2016, 37, 1088-1091.	2.2	10
44	Shubnikov-de Haas Oscillations of High-Mobility Holes in Monolayer and Bilayer WSe <sub>2</sub> . Physical Review Letters, 2016, 116, 086601.	4.5	28
45	Effects of Electrode Layer Band Structure on the Performance of Multilayer Graphene-hBN Graphene Interlayer Tunnel Field Effect Transistors. Nano Letters, 2016, 16, 4975-4981.	4.5	28
46	Giant Frictional Drag in Double Bilayer Graphene Heterostructures. Physical Review Letters, 2016, 117, 046803.	2.9	58
47	van der Waals Heterostructures with High Accuracy Rotational Alignment. Nano Letters, 2016, 16, 1989-1995.	4.5	477
48	Structural and Electrical Properties of MoTe <sub>2</sub> and MoSe <sub>2</sub> Grown by Molecular Beam Epitaxy. ACS Applied Materials & Interfaces, 2016, 8, 7396-7402.	4.0	189
49	Coherently Strained SiGe <sub>1-x</sub> Core-Shell Nanowire Heterostructures. Nano Letters, 2016, 16, 392-398.	4.5	26
50	Strain and Hole Gas Induced Raman Shifts in GeSi <sub>x</sub> Ge <sub>1-x</sub> Core-Shell Nanowires Using Tip-Enhanced Raman Spectroscopy. Nano Letters, 2015, 15, 4303-4310.	4.5	7
51	Intrinsic Disorder in Graphene on Transition Metal Dichalcogenide Heterostructures. Nano Letters, 2015, 15, 1925-1929.	4.5	37
52	Bilayer Graphene-Hexagonal Boron Nitride Heterostructure Negative Differential Resistance Interlayer Tunnel FET. IEEE Electron Device Letters, 2015, 36, 405-407.	2.2	50
53	Field Effect Transistors with Current Saturation and Voltage Gain in Ultrathin ReS <sub>2</sub> . ACS Nano, 2015, 9, 363-370.	7.3	169
54	Air Stable Doping and Intrinsic Mobility Enhancement in Monolayer Molybdenum Disulfide by Amorphous Titanium Suboxide Encapsulation. Nano Letters, 2015, 15, 4329-4336.	4.5	167

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55	Band Alignment in $WSe_2$ Graphene Heterostructures. ACS Nano, 2015, 9, 4527-4532.	7.3	138
56	High-Mobility Holes in Dual-Gated $WSe_2$ Field-Effect Transistors. ACS Nano, 2015, 9, 10402-10410.	7.3	232
57	Gate-Tunable Resonant Tunneling in Double Bilayer Graphene Heterostructures. Nano Letters, 2015, 15, 428-433.	4.5	166
58	Spectrally selective chiral silicon metasurfaces based on infrared Fano resonances. Nature Communications, 2014, 5, 3892.	5.8	397
59	Band Offset and Negative Compressibility in Graphene- $MoS_2$ Heterostructures. Nano Letters, 2014, 14, 2039-2045.	4.5	134
60	Radial modulation doping in core-shell nanowires. Nature Nanotechnology, 2014, 9, 116-120.	15.6	76
61	Oxidized Titanium as a Gate Dielectric for Graphene Field Effect Transistors and Its Tunneling Mechanisms. ACS Nano, 2014, 8, 10480-10485.	7.3	16
62	Atomistic simulation of the electronic states of adatoms in monolayer $MoS_2$ . Applied Physics Letters, 2014, 104, .	1.5	66
63	Chemical potential and quantum Hall ferromagnetism in bilayer graphene. Science, 2014, 345, 58-61.	6.0	120
64	The Role of Surface Oxygen in the Growth of Large Single-Crystal Graphene on Copper. Science, 2013, 342, 720-723.	6.0	977
65	Realization and Scaling of $\{m Ge\}_{1-x}\{m Si\}_x\{m Ge\}_x$ Core-Shell Nanowire n-FETs. IEEE Transactions on Electron Devices, 2013, 60, 4027-4033.	1.6	3
66	Vertically integrated double-layer on-chip silicon membranes for 1-to-12 waveguide fanouts. Applied Physics Letters, 2012, 100, 181102.	1.5	6
67	Scaling of $Al_2O_3$ dielectric for graphene field-effect transistors. Applied Physics Letters, 2012, 100, .	1.5	105
68	Direct Measurement of the Fermi Energy in Graphene Using a Double-Layer Heterostructure. Physical Review Letters, 2012, 108, 116404.	2.9	77
69	Field-effect transistors and intrinsic mobility in ultra-thin $MoSe_2$ layers. Applied Physics Letters, 2012, 101, .	1.5	494
70	Silicon based double-layer 1&#x00D7;12 multimode interference coupler for three-dimensional photonic integration. , 2012, , .		0
71	Germanium nMOSFETs with $GeO_2$ Passivation and n+/p Junctions Formed by Spin-On Dopants. , 2012, , .		0
72	Role of Confinement on Carrier Transport in $Ge/Si_xGe_{1-x}$ Core-shell Nanowires. Nano Letters, 2012, 12, 108-112.	4.5	34

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73	Coulomb drag and magnetotransport in graphene double layers. Solid State Communications, 2012, 152, 1283-1288.	0.9	56
74	Raman spectroscopy and strain mapping in individual $\text{Ge-Si}$ nanowires. Physical Review B, 2012, 86, .	1.1	28
75	Quantum Hall effect in Bernal stacked and twisted bilayer graphene grown on Cu by chemical vapor deposition. Physical Review B, 2012, 85, .	1.1	48
76	Self-aligned graphene field-effect transistors with polyethyleneimine doped source/drain access regions. Applied Physics Letters, 2012, 101, .	1.5	25
77	Fabrication of Three-Dimensional MIS Nano-Capacitor Based on Nanoimprinted Single Crystal Silicon Nanowire Arrays. Micro and Nanosystems, 2012, 4, 333-338.	0.3	3
78	High-Performance Ge nMOSFETs With $\text{Ge-Si}$ Junctions Formed by $\text{H}_2$ Spin-On Dopant. IEEE Electron Device Letters, 2011, 32, 1203-1205.	2.2	44
79	Low-Frequency Acoustic Phonon Temperature Distribution in Electrically Biased Graphene. Nano Letters, 2011, 11, 85-90.	4.5	63
80	Magnetotransport Properties of Quasi-Free-Standing Epitaxial Graphene Bilayer on SiC: Evidence for Bernal Stacking. Nano Letters, 2011, 11, 3624-3628.	4.5	39
81	CMOS-Compatible Synthesis of Large-Area, High-Mobility Graphene by Chemical Vapor Deposition of Acetylene on Cobalt Thin Films. ACS Nano, 2011, 5, 7198-7204.	7.3	109
82	High performance wire-array silicon solar cells. Progress in Photovoltaics: Research and Applications, 2011, 19, 307-312.	4.4	79
83	Spin-Polarized to Valley-Polarized Transition in Graphene Bilayers at $\frac{1}{2}$ in High Magnetic Fields. Physical Review Letters, 2011, 107, 016803.	2.9	50
84	Coulomb drag of massless fermions in graphene. Physical Review B, 2011, 83, .	1.1	165
85	Effective mass and spin susceptibility of dilute two-dimensional holes in GaAs. Physical Review B, 2011, 84, .	1.1	15
86	Bilayer Pseudospin Field-Effect Transistor: Applications to Boolean Logic. IEEE Transactions on Electron Devices, 2010, 57, 755-764.	1.6	36
87	$\text{Ge-Si}_{1-x}\text{Ge}_x$ Core-Shell Nanowire Tunneling Field-Effect Transistors. IEEE Transactions on Electron Devices, 2010, 57, 1883-1888.	1.6	30
88	Capacitance analysis of wire-array solar cell. , 2010, , .		0
89	On the fabrication of three-dimensional silicon-on-insulator based optical phased array for agile and large angle laser beam steering systems. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2010, 28, C6O1-C6O7.	0.6	19
90	Lateral Spin Injection in Germanium Nanowires. Nano Letters, 2010, 10, 3297-3301.	4.5	55

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91	Dielectric thickness dependence of carrier mobility in graphene with HfO <sub>2</sub> top dielectric. Applied Physics Letters, 2010, 97, .	1.5	97
92	Hall mobility measurements in enhancement-mode GaAs field-effect transistors with Al <sub>2</sub> O <sub>3</sub> gate dielectric. Applied Physics Letters, 2010, 97, .	1.5	22
93	Wire-textured silicon solar cells. , 2010, , .		1
94	Enhanced-Performance Germanium Nanowire Tunneling Field-Effect Transistors Using Flash-Assisted Rapid Thermal Process. IEEE Electron Device Letters, 2010, 31, 1359-1361.	2.2	23
95	Giant frictional drag in strongly interacting bilayers near filling factor one. Physical Review B, 2009, 79, .	1.1	10
96	Delay-Time-Enhanced Flat-Band Photonic Crystal Waveguides with Capsule-Shaped Holes on Silicon Nanomembrane. IEEE Journal of Selected Topics in Quantum Electronics, 2009, 15, 1510-1514.	1.9	3
97	Protein-Assembled Nanocrystal-Based Vertical Flash Memory Devices with Al <sub>2</sub> O <sub>3</sub> Integration. Journal of Electronic Materials, 2009, 38, 438-442.	1.0	2
98	Large-Area Synthesis of High-Quality and Uniform Graphene Films on Copper Foils. Science, 2009, 324, 1312-1314.	6.0	10,000
99	Negative Differential Resistance in Buried-Channel $\text{Ge}_x\text{C}_{1-x}$ pMOSFETs. IEEE Electron Device Letters, 2009, 30, 136-138.	2.2	4
100	Realization of a high mobility dual-gated graphene field-effect transistor with Al <sub>2</sub> O <sub>3</sub> dielectric. Applied Physics Letters, 2009, 94, .	1.5	827
101	Bilayer PseudoSpin Field-Effect Transistor (BiSFET): A Proposed New Logic Device. IEEE Electron Device Letters, 2009, 30, 158-160.	2.2	193
102	Valley susceptibility of interacting electrons and composite fermions. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 986-989.	1.3	3
103	Fabrication of Self-Aligned Enhancement-Mode $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$ MOSFETs With $\text{TaN}/\text{HfO}_2/\text{AlN}$ Gate Stack. IEEE Electron Device Letters, 2008, 29, 557-560.	2.2	43
104	Chemical and physical interface studies of the atomic-layer-deposited Al <sub>2</sub> O <sub>3</sub> on GaAs substrates. Applied Physics Letters, 2008, 92, .	1.5	34
105	Self-aligned inversion-type enhancement-mode GaAs metal-oxide-semiconductor field-effect transistor with Al <sub>2</sub> O <sub>3</sub> gate dielectric. Applied Physics Letters, 2008, 92, 203505.	1.5	28
106	Doping of Ge $\text{Si}_x\text{Ge}_{1-x}$ core-shell nanowires using low energy ion implantation. Applied Physics Letters, 2008, 93, 203108.	1.5	18
107	In-plane magnetic-field-induced metal-insulator transition in (311)A GaAs two-dimensional hole systems probed by thermopower. Physical Review B, 2007, 76, .	1.1	9
108	Strong Aharonov-Bohm oscillations in GaAs two-dimensional holes. Applied Physics Letters, 2007, 90, 152104.	1.5	19

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109	GaAs metal-oxide-semiconductor capacitors using atomic layer deposition of HfO <sub>2</sub> gate dielectric: Fabrication and characterization. Applied Physics Letters, 2007, 91, .	1.5	45
110	Pinning Modes and Interlayer Correlation in High-Magnetic-Field Bilayer Wigner Solids. Physical Review Letters, 2007, 99, 136804.	2.9	14
111	Spin susceptibility of interacting two-dimensional electrons with anisotropic effective mass. Physical Review B, 2007, 76, .	1.1	26
112	QUANTUM HALL EFFECT IN A MULTI-VALLEY TWO-DIMENSIONAL ELECTRON SYSTEM. International Journal of Modern Physics B, 2007, 21, 1388-1397.	1.0	8
113	Charge neutral counterflow transport at filling factor 1 in GaAs hole bilayers. Solid State Communications, 2007, 144, 405-408.	0.9	5
114	Zeeman splitting of interacting two-dimensional electrons with two effective masses. Solid State Communications, 2006, 140, 285-288.	0.9	2
115	Realization of a Linear Germanium Nanowire p-n Junction. Nano Letters, 2006, 6, 2070-2074.	4.5	81
116	Bilayer counterflow transport at filling factor 1 in the strong interacting regime. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 11-15.	1.3	2
117	Coulomb drag experiments in low density 2D hole bilayers. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 63-68.	1.3	0
118	Spin-dependent resistivity and quantum Hall ferromagnetism in two-dimensional electrons confined to AlAs quantum wells. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 89-92.	1.3	3
119	Thermopower evidence for Wigner crystallization in the insulating phase of two-dimensional GaAs bilayer hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2006, 34, 120-123.	1.3	1
120	Two-dimensional electrons occupying multiple valleys in AlAs. Physica Status Solidi (B): Basic Research, 2006, 243, 3629-3642.	0.7	109
121	High-mobility AlAs quantum wells with out-of-plane valley occupation. Applied Physics Letters, 2006, 89, 172118.	1.5	11
122	Doping of germanium nanowires grown in presence of PH <sub>3</sub> . Applied Physics Letters, 2006, 89, 263101.	1.5	65
123	Effect of oxide overlayer formation on the growth of gold catalyzed epitaxial silicon nanowires. Applied Physics Letters, 2006, 88, 103113.	1.5	27
124	Coulomb drag near the metal-insulator transition in two dimensions. Physical Review B, 2005, 71, .	1.1	21
125	Spin-Dependent Resistivity at Transitions between Integer Quantum Hall States. Physical Review Letters, 2005, 94, 176402.	2.9	17
126	Anomalous spin polarization of GaAs two-dimensional hole systems. Physical Review B, 2005, 72, .	1.1	40



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127	COUNTERFLOW MEASUREMENTS IN GaAs HOLE BILAYERS: POSSIBLE EVIDENCE FOR EXCITONIC CONDENSATION. , 2005, , .		0
128	Realization of an Interacting Two-Valley AlAs Bilayer System. Physical Review Letters, 2004, 92, 186404.	2.9	12
129	Negative differential Rashba effect in two-dimensional hole systems. Applied Physics Letters, 2004, 85, 3151-3153.	1.5	29
130	Spin Susceptibility of Two-Dimensional Electrons in Narrow AlAs Quantum Wells. Physical Review Letters, 2004, 92, 226401.	2.9	93
131	COUNTERFLOW MEASUREMENTS IN GaAs HOLE BILAYERS: POSSIBLE EVIDENCE FOR EXCITONIC CONDENSATION. International Journal of Modern Physics B, 2004, 18, 3685-3692.	1.0	2
132	Interacting GaAs bilayer hole systems with layer density imbalance. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 32-35.	1.3	0
133	Frictional drag between dilute two-dimensional hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 22, 300-303.	1.3	4
134	Ballistic Electron Transport in AlAs Quantum Wells. Physical Review Letters, 2004, 93, 246603.	2.9	35
135	Counterflow Measurements in Strongly Correlated GaAs Hole Bilayers: Evidence for Electron-Hole Pairing. Physical Review Letters, 2004, 93, 036802.	2.9	273
136	Magnetism and pseudo-magnetism in quantum Hall systems. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 20, 123-132.	1.3	4
137	Critical Resistance in the AlAs Quantum Hall Ferromagnet. Physical Review Letters, 2003, 91, 216802.	2.9	18
138	In-Plane Magnetodrag between Dilute Two-Dimensional Systems. Physical Review Letters, 2003, 90, 226801.	2.9	19
139	Role of Density Imbalance in an Interacting Bilayer Hole System. Physical Review Letters, 2003, 91, 076802.	2.9	36
140	Valley Splitting of AlAs Two-Dimensional Electrons in a Perpendicular Magnetic Field. Physical Review Letters, 2002, 89, 226805.	2.9	138
141	Enhanced electron mobility and high order fractional quantum Hall states in AlAs quantum wells. Applied Physics Letters, 2002, 80, 1583-1585.	1.5	60
142	QUANTUM HALL EFFECT IN AlAs 2D ELECTRON SYSTEMS. International Journal of Modern Physics B, 2002, 16, 2917-2922.	1.0	0
143	Spin Polarization and gFactor of a Dilute GaAs Two-Dimensional Electron System. Physical Review Letters, 2002, 88, 036805.	2.9	91
144	Hysteretic resistance spikes at transitions between quantum Hall ferromagnets in AlAs 2D electrons. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 36-38.	1.3	3

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145	Measurements of the effective g-factor in dilute GaAs 2D electrons. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 420-423.	1.3	0
146	Anomalous giant Rashba spin splitting in two-dimensional hole systems. Physica E: Low-Dimensional Systems and Nanostructures, 2002, 12, 428-431.	1.3	7
147	QUANTUM HALL EFFECT IN AlAs 2D ELECTRON SYSTEMS. , 2002, , .		0
148	In-Plane Magnetic Field-Induced Spin Polarization and Transition to Insulating Behavior in Two-Dimensional Hole Systems. Physical Review Letters, 2001, 86, 2858-2861.	2.9	99
149	Resistance Spikes at Transitions Between Quantum Hall Ferromagnets. , 2000, 290, 1546-1549.		148